

SCT2280KE

N-channel SiC power MOSFET

V_{DSS}	1200V
R _{DS(on)} (Typ.)	280m $Ω$
I _D	14A
P_D	108W

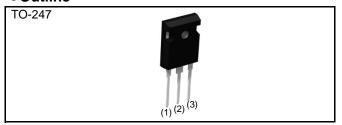
●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

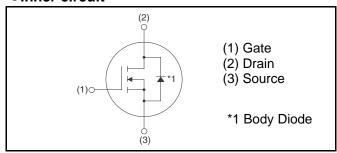
Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

Outline



•Inner circuit



Packaging specifications

	Packaging	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCT2280KE

●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		$V_{ extsf{DSS}}$	1200	V
Continuous drain current	T _c = 25°C	I _D *1	14	А
Continuous drain current	T _c = 100°C	I _D *1	10	А
Pulsed drain current		I _{D,pulse} *2	35	А
Gate - Source voltage (DC)		V_{GSS}	−6 to 22	V
Gate - Source surge voltage (T _{surge} < 300nsec)		V _{GSS-surge} *3	-10 to 26	V
Power dissipation (T _c = 25°C)		P_{D}	108	W
Junction temperature		T _j	175	°C
Range of storage temperature		T_{stg}	-55 to +175	°C

●Thermal resistance

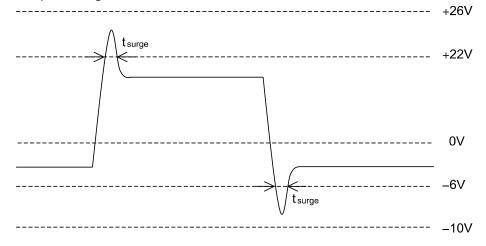
Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	1.07	1.39	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	1200	-	1	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I _{DSS}	T _j = 25°C	-	1	10	μΑ
		T _j = 150°C	-	2	-	
Gate - Source leakage current	$I_{\rm GSS+}$	$V_{GS} = +22V, V_{DS} = 0V$	1	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -6V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}$, $I_D = 1.4$ mA	1.6	2.8	4.0	V

^{*1} Limited only by maximum temperature allowed.

^{*3} Example of acceptable Vgs waveform



*4 Pulsed

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

●Electrical characteristics (T_a = 25°C)

Doromotor	Cymbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 18V, I_D = 4A$				
Static drain - source on - state resistance	R _{DS(on)} *4	T _j = 25°C	-	280	364	mΩ
		T _j = 125°C	-	388	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	17	-	Ω
Transconductance	g _{fs} *4	$V_{DS} = 10V$, $I_D = 4A$	-	1.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	667	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	27	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	5	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	41	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 400V, V_{GS} = 18V$	-	19	-	
Rise time	t _r *4	I _D = 4A	-	19	-	
Turn - off delay time	t _{d(off)} *4	$R_L = 100\Omega$	-	47	-	ns
Fall time	t _f *4	$R_G = 0\Omega$	-	29	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 600V, I_{D} = 4A$ $V_{GS} = 18V/0V$	-	57	-	1
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=500μH *E _{on} includes diode reverse recovery	-	20	-	μJ

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai i letei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Qg *4	V _{DD} = 400V	-	36	-	
Gate - Source charge	Q _{gs} *4	I _D = 4A	-	9	-	nC
Gate - Drain charge	Q _{gd} *4	V _{GS} = 18V	-	12	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 400V, I_D = 4A$	-	9.8	-	V

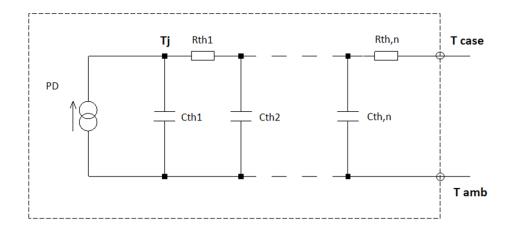
●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _c = 25°C	-	-	14	А
Inverse diode direct current, pulsed	I _{SM} *2	-1 _c = 25°C	-	-	35	А
Forward voltage	V _{SD} *4	$V_{GS} = 0V$, $I_S = 4A$	-	4.0	-	V
Reverse recovery time	t _{rr} *4		ı	22	ı	ns
Reverse recovery charge	Q _{rr} *4	I _F = 4A, V _R = 400V di/dt = 160A/μs	-	21	-	nC
Peak reverse recovery current	I _{rrm} *4		-	2.0	-	Α

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	100m	
R _{th2}	662m	K/W
R _{th3}	304m	

Symbol	Value	Unit
C _{th1}	861μ	
C _{th2}	2.84m	Ws/K
C _{th3}	55.9m	



•Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

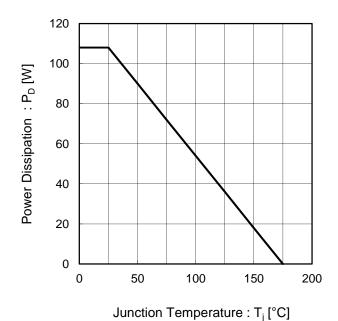
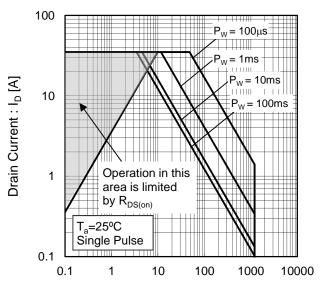
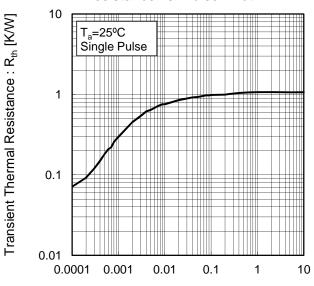


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

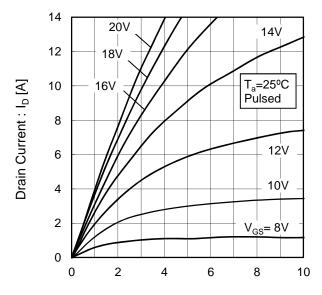
Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



Pulse Width : P_W [s]

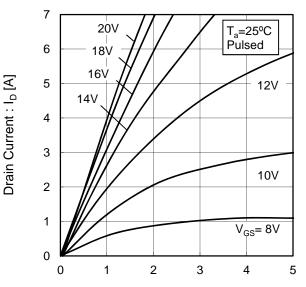
• Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)



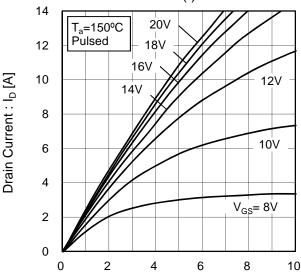
Drain - Source Voltage : V_{DS} [V]

Fig.5 Typical Output Characteristics(II)



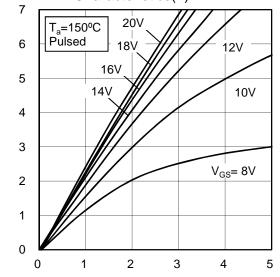
Drain - Source Voltage : V_{DS} [V]

Fig.6 T_j = 150°C Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

Fig.7 T_j = 150°C Typical Output Characteristics(II)

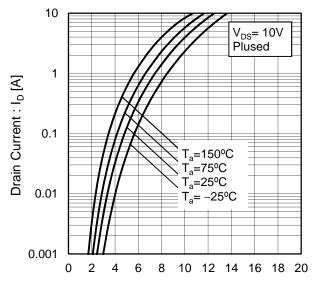


Drain - Source Voltage : V_{DS} [V]

Drain Current : I_D [A]

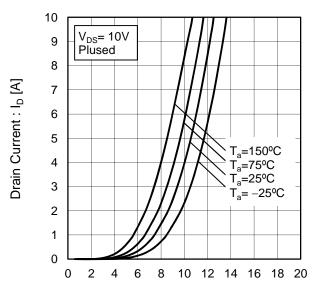
• Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)



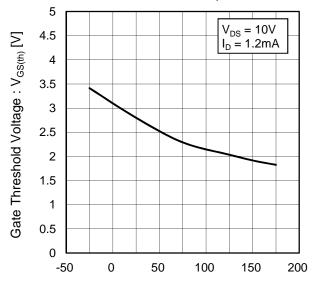
Gate - Source Voltage : V_{GS} [V]

Fig.9 Typical Transfer Characteristics (II)



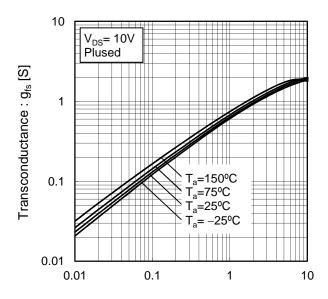
Gate - Source Voltage : V_{GS} [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

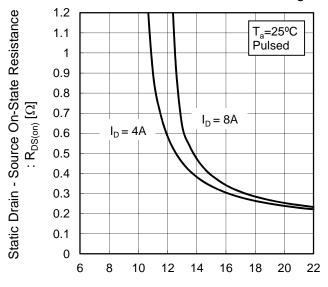
Fig.11 Transconductance vs. Drain Current



Drain Current : I_D [A]

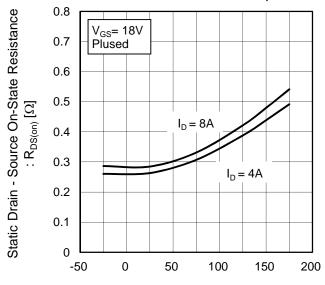
• Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



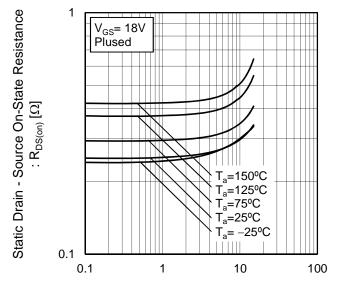
Gate - Source Voltage : $V_{GS}[V]$

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current : I_D [A]

•Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage 10000 1000 Capacitance: C [pF] 100 C_{oss} 10 T_a=25°C = 1MHz

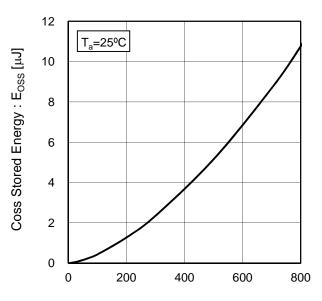
Drain - Source Voltage : V_{DS} [V]

10

100

1000

Fig.16 Coss Stored Energy



Drain - Source Voltage : V_{DS} [V]

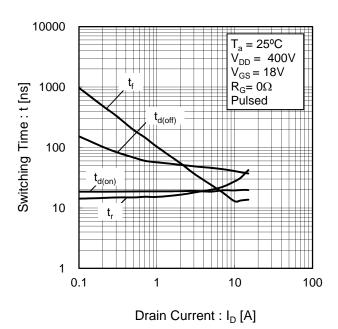
Fig.18 Dynamic Input Characteristics

Fig.17 Switching Characteristics

= 0V

1

0.1



 $T_a = 25^{\circ}C$ $V_{DD} = 400V$ $I_D = 4A$ Pulsed 15

20

Gate - Source Voltage : V_{GS} [V]

10 5 0 5 0 10 15 20 25 30 35 40

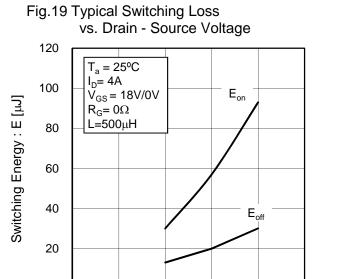
Total Gate Charge : Q_q [nC]

0

0

200

•Electrical characteristic curves



Drain - Source Voltage : V_{DS} [V]

600

800

1000

400

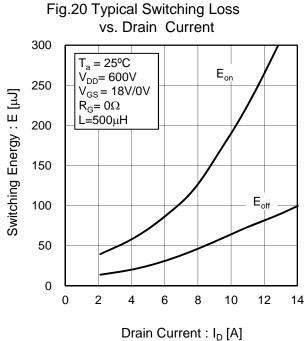
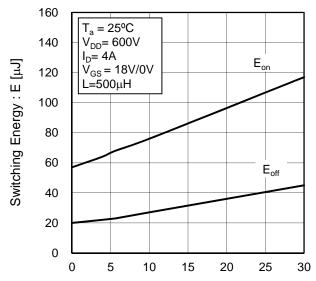
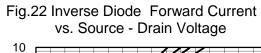


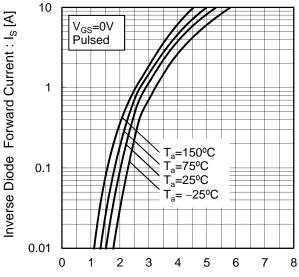
Fig.21 Typical Switching Loss vs. External Gate Resistance



External Gate Resistance : $R_G [\Omega]$

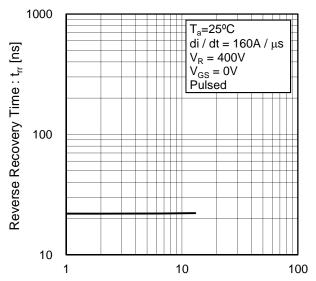
•Electrical characteristic curves





Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

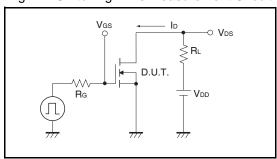


Fig.2-1 Gate Charge Measurement Circuit

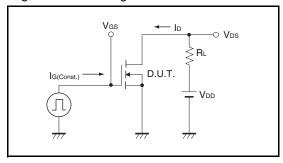


Fig.3-1 Switching Energy Measurement Circuit

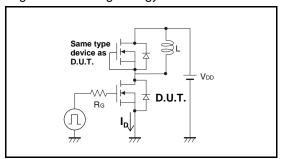


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

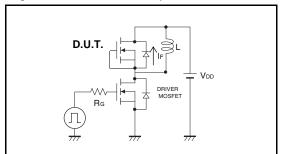


Fig.1-2 Switching Waveforms

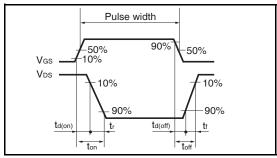


Fig.2-2 Gate Charge Waveform

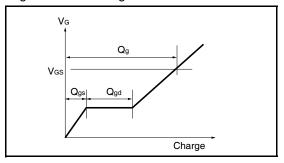
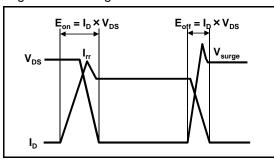
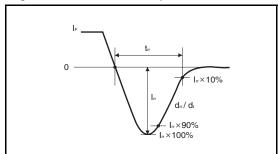


Fig.3-2 Switching Waveforms





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